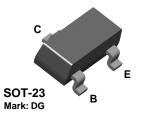


BCW68G

FAIRCHILD SEMICONDUCTOR IM



PNP General Purpose Amplifier

This device is designed for general purpose amplifier and switching applications at currents to 500 mA. Sourced from Process 63.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V _{CEO}	Collector-Emitter Voltage	45	V	
V _{CBO}	Collector-Base Voltage	60	V	
V _{EBO}	Emitter-Base Voltage	5.0	V	
Ic	Collector Current - Continuous	800	mA	
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C	

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Мах	Units
		*BCW68G	
PD	Total Device Dissipation	350	mW
	Derate above 25°C	2.8	mW/°C
$R_{ ext{ heta}JA}$	Thermal Resistance, Junction to Ambient	357	°C/W

*Device mounted on FR-4 PCB 40 mm X 40 mm X 1.5 mm.

©1997 Fairchild Semiconductor Corporation

Π	
0	
٤	
6	
8	
G	

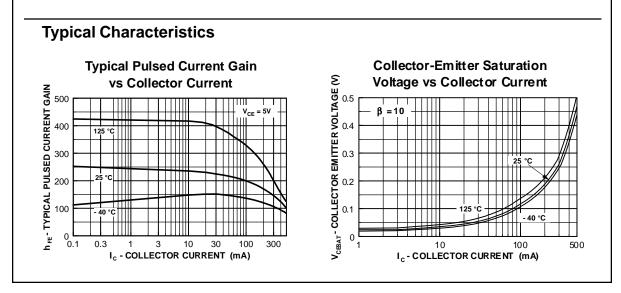
PNP General Purpose Amplifier (continued)

Electri	Electrical Characteristics TA = 25°C unless otherwise noted				
Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHAF	RACTERISTICS	·			
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0$	45		V
V _{(BR)CES}	Collector-Base Breakdown Voltage	I _C = 10 μA	60		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_{C} = 100 \ \mu A, I_{E} = 0$	60		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_{\rm E} = 10 \ \mu A, \ I_{\rm C} = 0$	5.0		V
ICES	Collector-Cutoff Current	V _{CE} = 45 V V _{CE} = 45 V, T _A = 150 °C		20 10	nA μA
I _{EBO}	Emitter-Cutoff Current	$V_{EB} = 4.0 \text{ V}$		20	nA
	ACTERISTICS	1 10 mA 1/ 1 0 1/	100	1	<u>г</u>
h _{FE}	DC Current Gain	$I_{C} = 10 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_{C} = 100 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_{C} = 300 \text{ mA}, V_{CE} = 1.0 \text{ V}$	120 160 60	400	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_{\rm C} = 300 \text{ mA}, I_{\rm B} = 30 \text{ mA}$		1.5	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	$I_{\rm C} = 500 \text{ mA}, I_{\rm B} = 50 \text{ mA}$		2.0	V
	GNAL CHARACTERISTICS				
f _T	Current Gain - Bandwidth Product	$I_{C} = 20 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 100 MHz	100		MHz
Cobo	Ouput Capacitance	$V_{CB} = 10 \text{ V}, \text{ I}_{E} = 0, \text{ f} = 1.0 \text{ MHz}$		18	pF
Cibo	Input Capacitance	$V_{EB} = 0.5 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$		105	pF
NF	Noise Figure	$ I_{C} = 0.2 \text{ mA V}, V_{CE} = 5.0 \text{ V}, \\ R_{S} = 1.0 \text{ k}\Omega, f = 1.0 \text{ kHz}, \\ B_{W} = 200 \text{ Hz} $		10	dB

NOTE: All voltages (V) and currents (A) are negative polarity for PNP transistors.

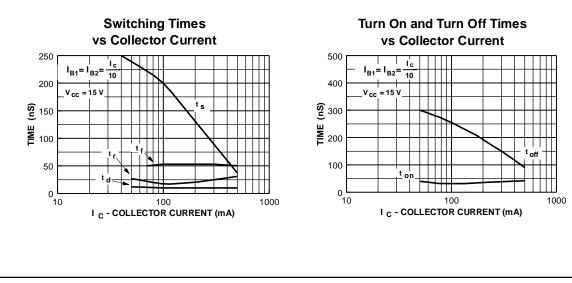
Spice Model

PNP (Is=650.6E-18 Xti=3 Eg=1.11 Vaf=115.7 Bf=231.7 Ne=1.829 Ise=54.81f Ikf=1.079 Xtb=1.5 Br=3.563 Nc=2 Isc=0 Ikr=0 Rc=.715 Cjc=14.76p Mjc=.5383 Vjc=.75 Fc=.5 Cje=19.82p Mje=.3357 Vje=.75 Tr=111.3n Tf=603.7p Itf=.65 Vtf=5 Xtf=1.7 Rb=10)



BCW68G

PNP General Purpose Amplifier (continued) **Typical Characteristics** (continued) **Base-Emitter Saturation** Base Emitter ON Voltage vs Voltage vs Collector Current 1 **I** 0.8 0.8 0.0 1 **Collector Current** 0.6 V BE(ON)- BASE EMITTER 0.4 125 °C $\beta = 10$ V_{CE} = 5V 0.2 0 L 0.1 100 500 1 10 25 I c- COLLECTOR CURRENT (mA) I_c-COLLECTOR CURRENT (mA) **Input and Output Capacitance Collector-Cutoff Current** vs Reverse Bias Voltage vs Ambient Temperature 20 **CAPACITANCE (pF)** Λ 0 -0.1 75 100 125 -10 - 50 -1 TA- AMBIENT TEMPERATURE (° C) **REVERSE BIAS VOLTAGE (V)**



V BESAT - BAS

COLLECTOR CURRENT (nA)

0

1

25 °C

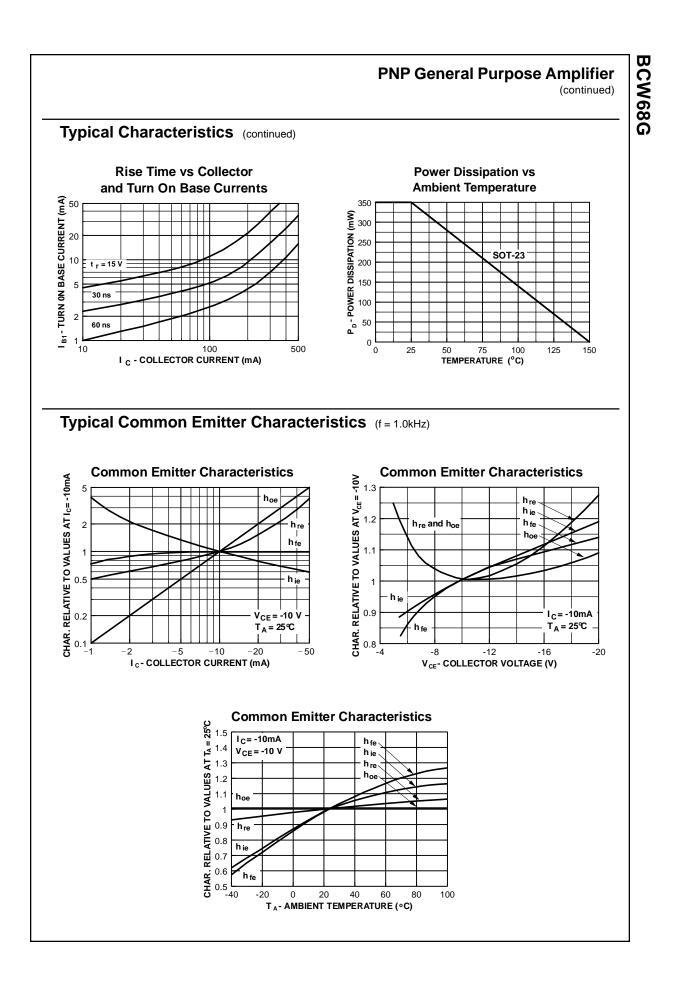
10

125 °C

ċc 40

 $V_{CB} = 35V$

50



BCW68G

(continued)

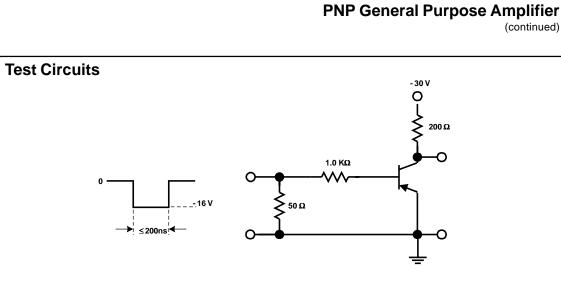


FIGURE 1: Saturated Turn-On Switching Time Test Circuit

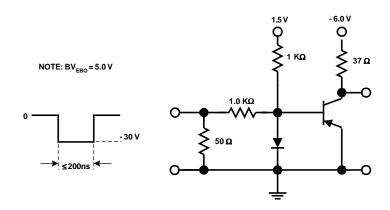
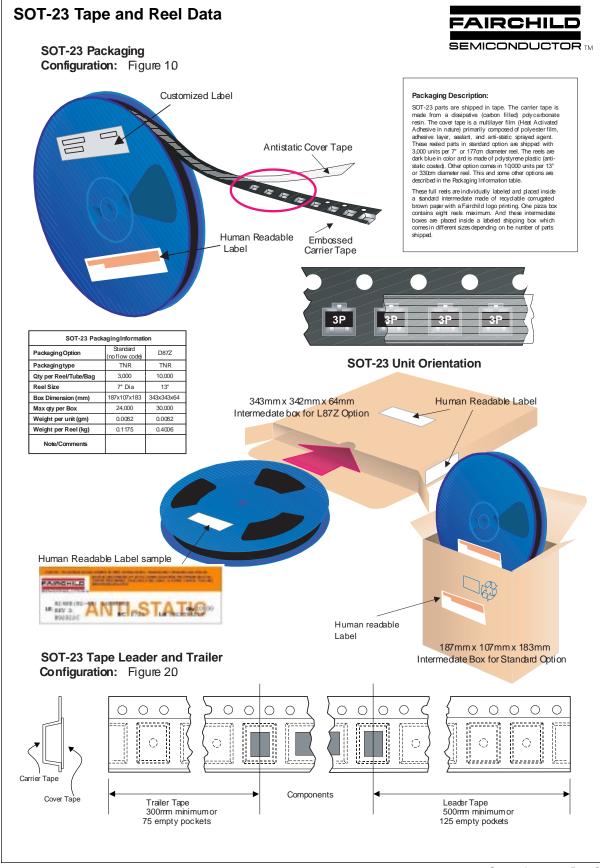
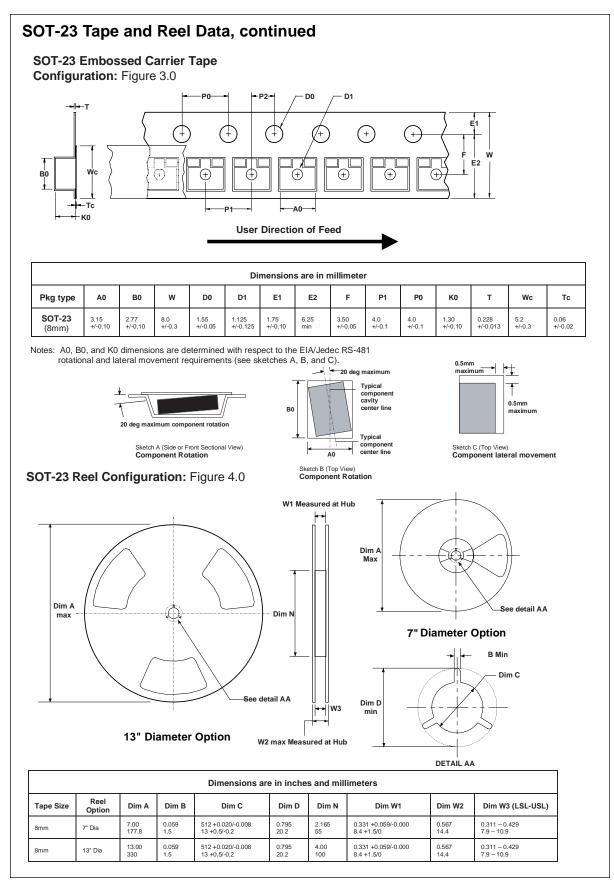


FIGURE 2: Saturated Turn-Off Switching Time Test Circuit

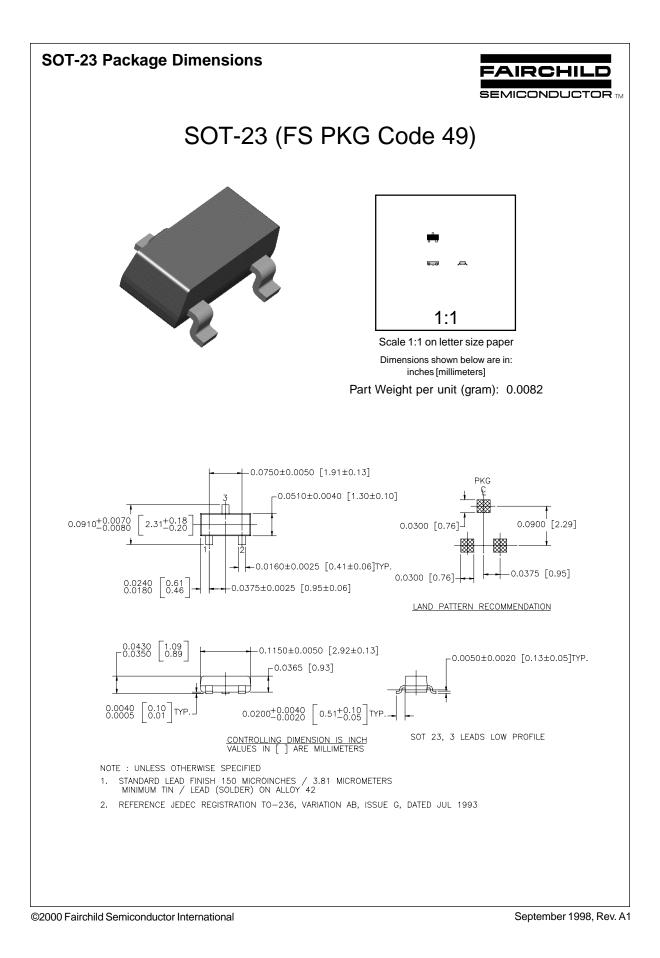


©2000 Fairchild Semiconductor International

September 1999, Rev. C



September 1999, Rev. C



Downloaded from Elcodis.com electronic components distributor

TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACExTM BottomlessTM CoolFETTM $CROSSVOLT^{TM}$ DOMETM E²CMOSTM EnSignaTM FACTTM FACT Quiet SeriesTM FAST ® FASTr[™] GlobalOptoisolator[™] GTO[™] HiSeC[™] ISOPLANAR[™] MICROWIRE[™] OPTOLOGIC[™] OPTOPLANAR[™] PACMAN[™] POP[™] PowerTrench® QFET™ QS™ QT Optoelectronics™ Quiet Series™ SILENT SWITCHER® SMART START™ SuperSOT™-3 SuperSOT™-6 SuperSOT™-8 SyncFET™ TinyLogic™ UHC™ VCX™

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user. 2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.
Obsolete	Not In Production	that has been discontinued by Fairchild semicon